

# Alessandra Leonhardt

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2926903/publications.pdf>

Version: 2024-02-01

14  
papers

275  
citations

933447

10  
h-index

1125743

13  
g-index

14  
all docs

14  
docs citations

14  
times ranked

522  
citing authors

#	ARTICLE	IF	CITATIONS
1	Layer-controlled epitaxy of 2D semiconductors: bridging nanoscale phenomena to wafer-scale uniformity. <i>Nanotechnology</i> , 2018, 29, 425602.	2.6	48
2	Material-Selective Doping of 2D TMDC through Al <sub>x</sub> O <sub>y</sub> Encapsulation. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 42697-42707.	8.0	37
3	Improving MOCVD MoS <sub>2</sub> Electrical Performance: Impact of Minimized Water and Air Exposure Conditions. <i>IEEE Electron Device Letters</i> , 2017, 38, 1606-1609.	3.9	33
4	Multicomponent Covalent Chemical Patterning of Graphene. <i>ACS Nano</i> , 2021, 15, 10618-10627.	14.6	31
5	Devices and Circuits Using Novel 2-D Materials: A Perspective for Future VLSI Systems. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2019, 27, 1486-1503.	3.1	30
6	Growth of Millimeter-Sized Graphene Single Crystals on Al <sub>2</sub> O <sub>3</sub> (0001)/Pt(111) Template Wafers Using Chemical Vapor Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, M195-M200.	1.8	20
7	Graphene based Van der Waals contacts on MoS <sub>2</sub> field effect transistors. <i>2D Materials</i> , 2021, 8, 015003.	4.4	15
8	The Role of Nonidealities in the Scaling of MoS <sub>2</sub> FETs. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4635-4640.	3.0	14
9	Understanding ambipolar transport in MoS <sub>2</sub> field effect transistors: the substrate is the key. <i>Nanotechnology</i> , 2021, 32, 135202.	2.6	14
10	(Invited) Internal Photoemission of Electrons from 2-Dimensional Semiconductors. <i>ECS Transactions</i> , 2017, 80, 191-201.	0.5	12
11	Use of the Indirect Photoluminescence Peak as an Optical Probe of Interface Defectivity in MoS <sub>2</sub> . <i>Advanced Materials Interfaces</i> , 2020, 7, 2000413.	3.7	10
12	Relation between film thickness and surface doping of MoS <sub>2</sub> based field effect transistors. <i>APL Materials</i> , 2018, 6, .	5.1	9
13	A novel self-aligned double patterning integrated with Ga <sup>+</sup> focused ion beam milling for silicon nanowire definition. <i>Microelectronic Engineering</i> , 2021, 237, 111493.	2.4	2
14	Contact Interface Characterization of Graphene contacted MoS <sub>2</sub> FETs. , 2021, , .		0